

# PESDxS1UB series

ESD protection diodes in SOD 523 package

Rev. 01 — 14 June 2004

Product data sheet

## 1. Product profile

### 1.1 General description

Unidirectional ESD protection diode in a SOD523 plastic package designed to protect one transmission or data line from the damage caused by ESD (Electro Static Discharge) and other transients.

### 1.2 Features

- Unidirectional ESD protection of one line
- Max. peak pulse power:  $P_{PP} = 330\text{ W}$  at  $t_p = 8/20\text{ }\mu\text{s}$
- Low clamping voltage:  $V_{CL} = 20\text{ V}$  at  $I_{PP} = 18\text{ A}$
- Ultra low leakage current:  $I_{RM} < 700\text{ nA}$
- ESD protection  $> 23\text{ kV}$
- IEC 61000-4-2, level 4 (ESD)
- IEC 61000-4-5 (surge);  $I_{PP} = 18\text{ A}$  at  $t_p = 8/20\text{ }\mu\text{s}$ .

### 1.3 Applications

- Computers and peripherals
- Communication systems
- Audio and video equipment
- Data lines
- CAN bus protection.

### 1.4 Quick reference data

Table 1: Quick reference data

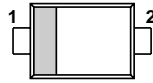

| Symbol    | Parameter                | Conditions | Value | Unit |
|-----------|--------------------------|------------|-------|------|
| $V_{RWM}$ | reverse standoff voltage |            |       |      |
|           | PESD3V3S1UB              |            | 3.3   | V    |
|           | PESD5V0S1UB              |            | 5     | V    |
|           | PESD12VS1UB              |            | 12    | V    |
|           | PESD15VS1UB              |            | 15    | V    |
|           | PESD24VS1UB              |            | 24    | V    |

Table 1: Quick reference data ...continued

| Symbol | Parameter                 | Conditions                              | Value | Unit |
|--------|---------------------------|---|-------|------|
| $C_d$  | diode capacitance         | $V_R = 0\text{ V}$ ; $f = 1\text{ MHz}$ |       |      |
|        | PESD3V3S1UB               |   | 207   | pF   |
|        | PESD5V0S1UB               |   | 152   | pF   |
|        | PESD12VS1UB               |   | 38    | pF   |
|        | PESD15VS1UB               |   | 32    | pF   |
|        | PESD24VS1UB               |   | 23    | pF   |
|        | number of protected lines |   | 1     |      |

## 2. Pinning information

Table 2: Discrete pinning

| Pin | Description | Simplified outline   | Symbol  |
|-----|-------------|--|---|
| 1   | cathode     |  <p>Top view</p> |  <p>sym035</p> |
| 2   | anode       |  |   |

[1] The marking bar indicates the cathode.

## 3. Ordering information

Table 3: Ordering information

| Type number | Package |  |         |
|-------------|---------|--|---------|
|             | Name    | Description                              | Version |
| PESDxS1UB   | SC -79  | plastic surface mounted package; 2 leads | SOD523  |

## 4. Marking

Table 4: Marking

| Type number | Marking code |
|-------------|--------------|
| PESD3V3S1UB | N1           |
| PESD5V0S1UB | N2           |
| PESD12VS1UB | N3           |
| PESD15VS1UB | N4           |
| PESD24VS1UB | N5           |

## 5. Limiting values

**Table 5: Limiting values**

*In accordance with the Absolute Maximum Rating System (IEC 60134).*

| Symbol           | Parameter                     | Conditions   | Min | Max  | Unit |
|------------------|-------------------------------|--------------|-----|------|------|
| P <sub>PP</sub>  | peak pulse power              | 8/20 $\mu$ s | [1] |      |      |
|                  | PESD3V3S1UB                   |              | -   | 330  | W    |
|                  | PESD5V0S1UB                   |              | -   | 260  | W    |
|                  | PESD12VS1UB                   |              | -   | 180  | W    |
|                  | PESD15VS1UB                   |              | -   | 160  | W    |
|                  | PESD24VS1UB                   |              | -   | 160  | W    |
| I <sub>PP</sub>  | peak pulse current            | 8/20 $\mu$ s | [1] |      |      |
|                  | PESD3V3S1UB                   |              | -   | 18   | A    |
|                  | PESD5V0S1UB                   |              | -   | 15   | A    |
|                  | PESD12VS1UB                   |              | -   | 5    | A    |
|                  | PESD15VS1UB                   |              | -   | 5    | A    |
|                  | PESD24VS1UB                   |              | -   | 3    | A    |
| T <sub>j</sub>   | junction temperature          |              | -   | 150  | °C   |
| T <sub>amb</sub> | operating ambient temperature |              | -65 | +150 | °C   |
| T <sub>stg</sub> | storage temperature           |              | -65 | +150 | °C   |

[1] Non-repetitive current pulse 8/20  $\mu$ s exponentially decay waveform; see [Figure 1](#).

**Table 6: ESD maximum ratings**

| Symbol | Parameter                          | Conditions                        | Min | Max | Unit |
|--------|------------------------------------|-----------------------------------|-----|-----|------|
| ESD    | electrostatic discharge capability | IEC 61000-4-2 (contact discharge) | [1] |     |      |
|        | PESD3V3S1UB                        |                                   | -   | 30  | kV   |
|        | PESD5V0S1UB                        |                                   | -   | 30  | kV   |
|        | PESD12VS1UB                        |                                   | -   | 30  | kV   |
|        | PESD15VS1UB                        |                                   | -   | 30  | kV   |
|        | PESD24VS1UB                        |                                   | -   | 23  | kV   |
|        | PESDxS1UB series                   | HBM MIL-STD883                    | -   | 10  | kV   |

[1] Device stressed with ten non-repetitive Electro Static Discharge (ESD) pulses; see [Figure 2](#).

**Table 7: ESD standards compliance**

| ESD Standard                 | Conditions                      |
|------------------------------|---------------------------------|
| IEC 61000-4-2, level 4 (ESD) | > 15 kV (air); > 8 kV (contact) |
| HBM MIL-STD883, class 3      | > 4 kV                          |

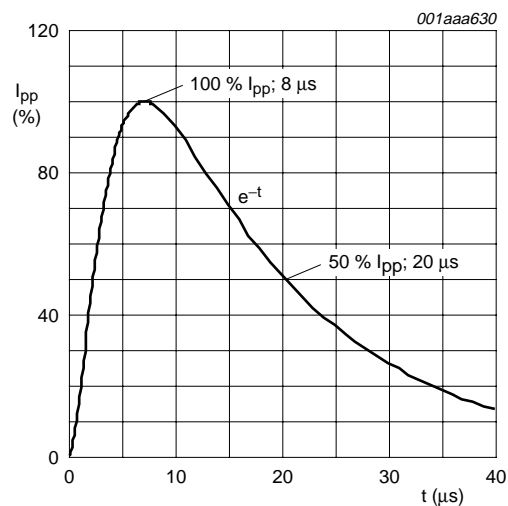


Fig 1. 8/20  $\mu$ s pulse waveform according to IEC 61000-4-5.

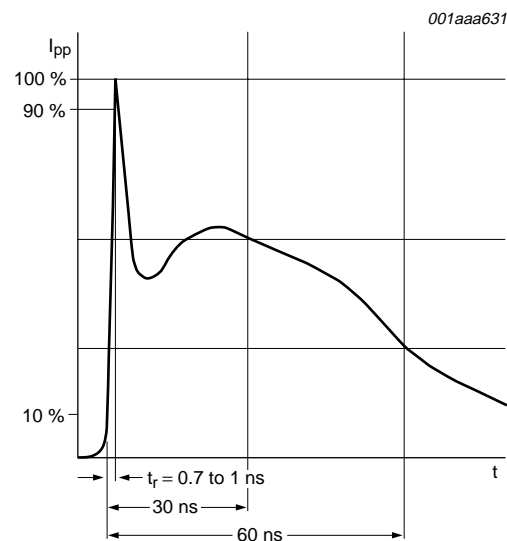


Fig 2. Electro Static Discharge (ESD) pulse waveform according to IEC 61000-4-2.

## 6. Characteristics

**Table 8: Characteristics**

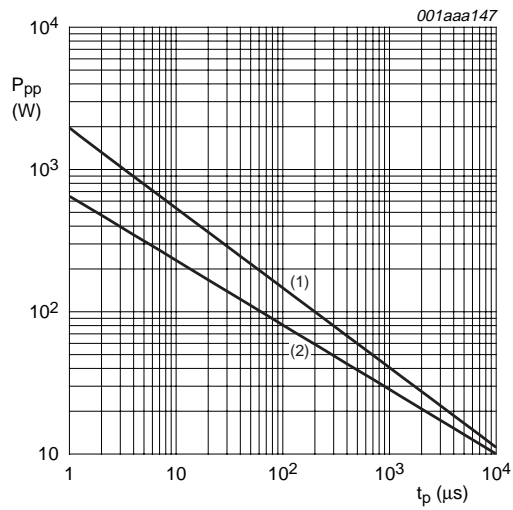
$T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified.

| Symbol      | Parameter                | Conditions  | Min                 | Typ  | Max  | Unit          |
|-------------|--------------------------|---|---------------------|------|------|---------------|
| $V_{RWM}$   | reverse standoff voltage |   |                     |      |      |               |
|             | PESD3V3S1UB              |   | -                   | -    | 3.3  | V             |
|             | PESD5V0S1UB              |   | -                   | -    | 5    | V             |
|             | PESD12VS1UB              |   | -                   | -    | 12   | V             |
|             | PESD15VS1UB              |   | -                   | -    | 15   | V             |
|             | PESD24VS1UB              |   | -                   | -    | 24   | V             |
| $I_{RM}$    | reverse leakage current  | see <a href="#">Figure 7</a>  |                     |      |      |               |
|             | PESD3V3S1UB              | $V_{RWM} = 3.3\text{ V}$  | -                   | 0.7  | 2    | $\mu\text{A}$ |
|             | PESD5V0S1UB              | $V_{RWM} = 5\text{ V}$  | -                   | 0.1  | 1    | $\mu\text{A}$ |
|             | PESD12VS1UB              | $V_{RWM} = 12\text{ V}$   | -                   | < 1  | 50   | nA            |
|             | PESD15VS1UB              | $V_{RWM} = 15\text{ V}$   | -                   | < 1  | 50   | nA            |
|             | PESD24VS1UB              | $V_{RWM} = 24\text{ V}$   | -                   | < 1  | 50   | nA            |
| $V_{BR}$    | breakdown voltage        | $I_R = 5\text{ mA}$   |                     |      |      |               |
|             | PESD3V3S1UB              |   | 5.2                 | 5.6  | 6.0  | V             |
|             | PESD5V0S1UB              |   | 6.4                 | 6.8  | 7.2  | V             |
|             | PESD12VS1UB              |   | 14.7                | 15.0 | 15.3 | V             |
|             | PESD15VS1UB              |   | 17.6                | 18.0 | 18.4 | V             |
|             | PESD24VS1UB              |   | 26.5                | 27.0 | 27.5 | V             |
| $C_d$       | diode capacitance        | $V_R = 0\text{ V}$ ; $f = 1\text{ MHz}$ ;<br>see <a href="#">Figure 5</a> and <a href="#">6</a> |                     |      |      |               |
|             | PESD3V3S1UB              |   | -                   | 207  | 300  | pF            |
|             | PESD5V0S1UB              |   | -                   | 152  | 200  | pF            |
|             | PESD12VS1UB              |   | -                   | 38   | 75   | pF            |
|             | PESD15VS1UB              |   | -                   | 32   | 70   | pF            |
|             | PESD24VS1UB              |   | -                   | 23   | 50   | pF            |
| $V_{(CL)R}$ | clamping voltage         |   | <a href="#">[1]</a> |      |      |               |
|             | PESD3V3S1UB              | $I_{PP} = 1\text{ A}$   | -                   | -    | 7    | V             |
|             |                          | $I_{PP} = 18\text{ A}$  | -                   | -    | 20   | V             |
|             | PESD5V0S1UB              | $I_{PP} = 1\text{ A}$   | -                   | -    | 9    | V             |
|             |                          | $I_{PP} = 15\text{ A}$  | -                   | -    | 20   | V             |
|             | PESD12VS1UB              | $I_{PP} = 1\text{ A}$   | -                   | -    | 19   | V             |
|             |                          | $I_{PP} = 5\text{ A}$   | -                   | -    | 35   | V             |
|             | PESD15VS1UB              | $I_{PP} = 1\text{ A}$   | -                   | -    | 23   | V             |
|             |                          | $I_{PP} = 5\text{ A}$   | -                   | -    | 40   | V             |
|             | PESD24VS1UB              | $I_{PP} = 1\text{ A}$   | -                   | -    | 36   | V             |
|             |                          | $I_{PP} = 3\text{ A}$   | -                   | -    | 70   | V             |

**Table 8: Characteristics ...continued** $T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified.

| Symbol     | Parameter               | Conditions            | Min | Typ | Max | Unit     |
|------------|-------------------------|-----------------------|-----|-----|-----|----------|
| $R_{diff}$ | differential resistance |                       |     |     |     |          |
|            | PESD3V3S1UB             | $I_R = 1\text{ mA}$   | -   | -   | 400 | $\Omega$ |
|            | PESD5V0S1UB             | $I_R = 1\text{ mA}$   | -   | -   | 80  | $\Omega$ |
|            | PESD12VS1UB             | $I_R = 1\text{ mA}$   | -   | -   | 200 | $\Omega$ |
|            | PESD15VS1UB             | $I_R = 1\text{ mA}$   | -   | -   | 225 | $\Omega$ |
|            | PESD24VS1UB             | $I_R = 0.5\text{ mA}$ | -   | -   | 300 | $\Omega$ |

[1] Non-repetitive current pulse 8/20  $\mu\text{s}$  exponentially decay waveform; see [Figure 1](#).

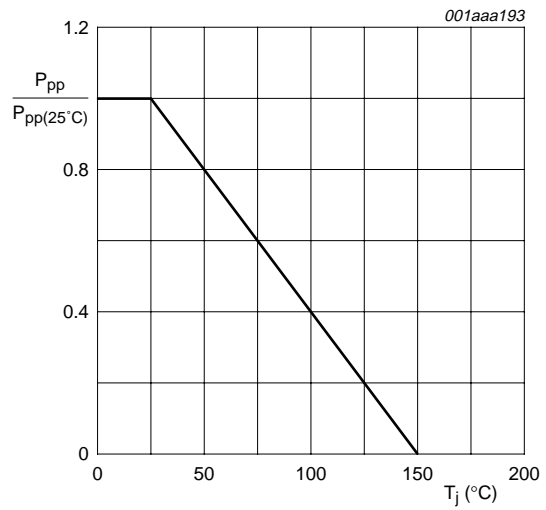


$T_{amb} = 25\text{ °C}$

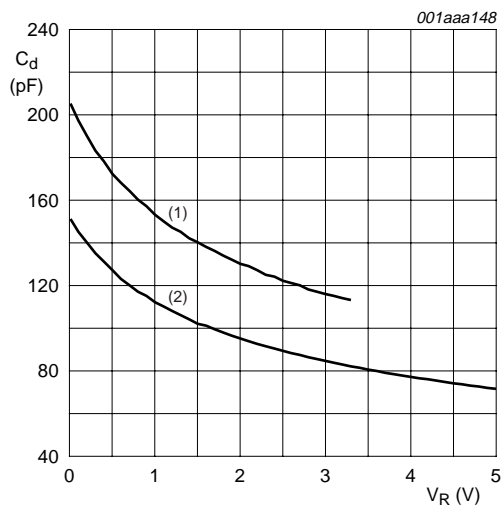
$t_p = 8/20\text{ μs}$  exponentially decay waveform, see Figure 1.

- (1) PESD3VS1UB and PESD5V0S1UB.
- (2) PESD12VS1UB, PESD15VS1UB; PESD24VS1UB.

**Fig 3. Peak pulse power dissipation as a function of pulse time; typical values.**



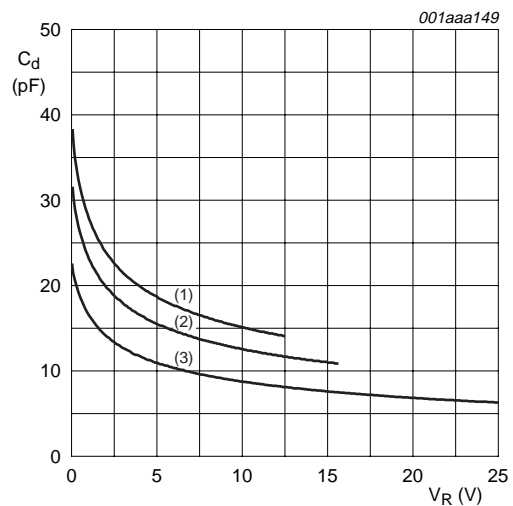
**Fig 4. Relative variation of peak pulse power as a function of junction temperature; typical values.**



$f = 1\text{ MHz}$ ;  $T_{amb} = 25\text{ °C}$

- (1) PESD3VS1UB.
- (2) PESD5V0S1UB.

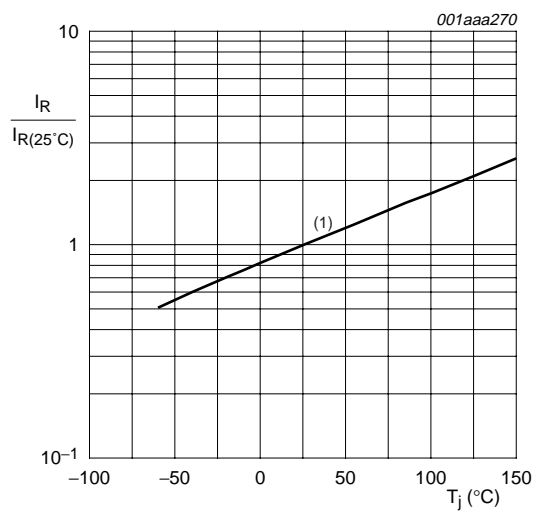
**Fig 5. Diode capacitance as a function of reverse voltage; typical values.**



$f = 1\text{ MHz}$ ;  $T_{amb} = 25\text{ °C}$

- (1) PESD12VS1UB.
- (2) PESD15VS1UB.
- (3) PESD24VS1UB.

**Fig 6. Diode capacitance as a function of reverse voltage; typical values.**



- (1) PESD3V3S1UB;  $V_{RWM} = 3.3$  V.  
 PESD5V0S1UB;  $V_{RWM} = 5$  V.  
 $I_R$  is less than 10 nA at 150 °C for:  
 PESD12VS1UB;  $V_{RWM} = 12$  V.  
 PESD15VS1UB;  $V_{RWM} = 15$  V.  
 PESD24VS1UB;  $V_{RWM} = 24$  V.

**Fig 7. Relative variation of reverse leakage current as a function of junction temperature; typical values.**



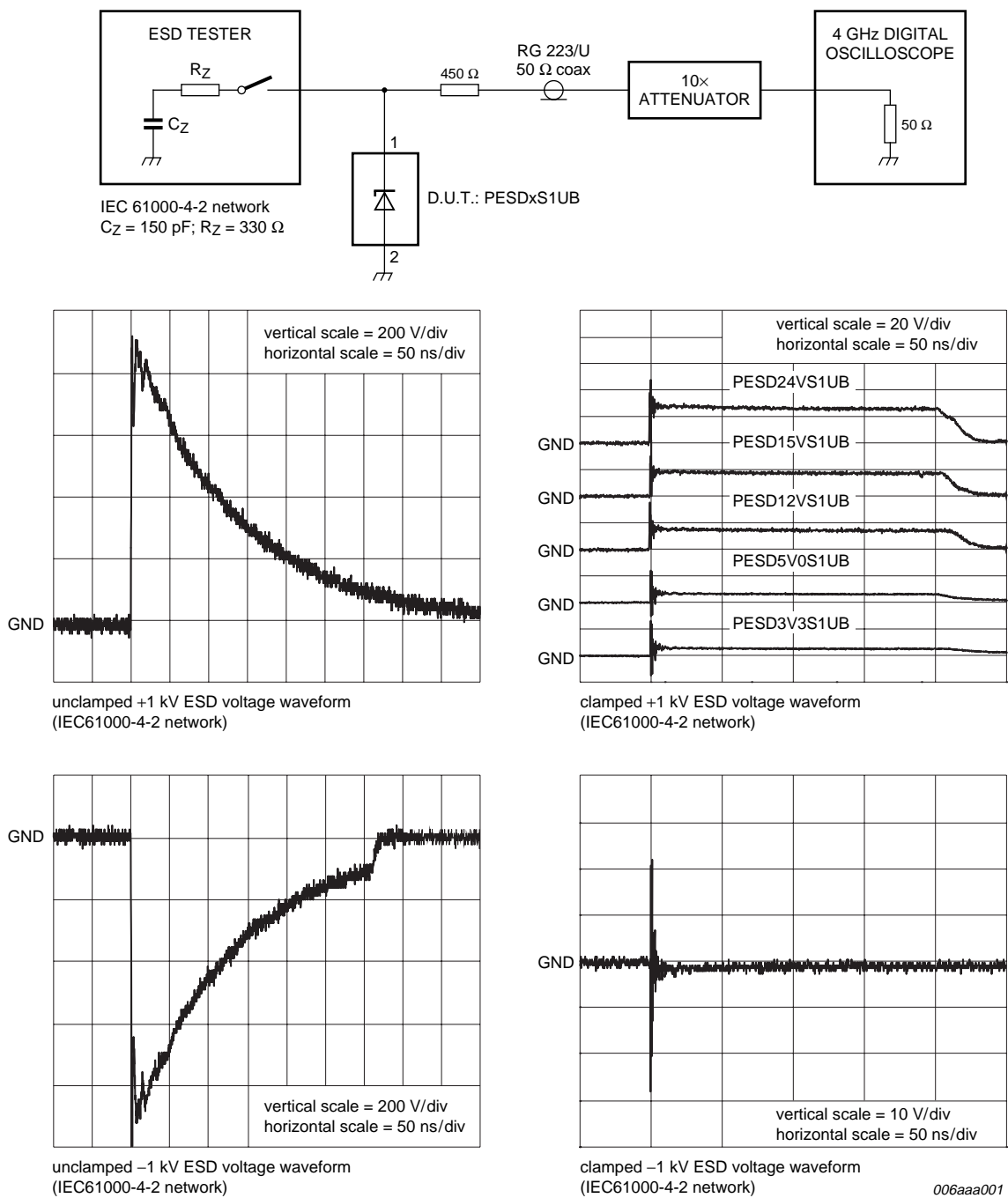
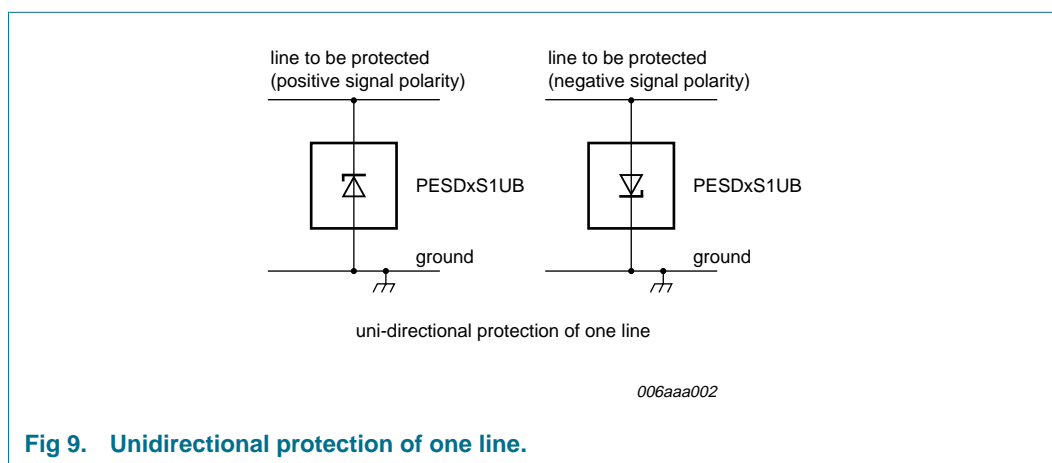


Fig 8. ESD clamping test set-up and waveforms.

## 7. Application information

The PESDxS1UB series is designed for unidirectional protection of one single data line from the damage caused by ESD (Electro Static Discharge) and Surge Pulses. The PESDxS1UB series may be used on lines where the signal polarity is above or below ground. The PESDxS1UB series provides a surge capability of up to 330 Watts per line for a 8/20  $\mu$ s waveform.



**Fig 9. Unidirectional protection of one line.**

### Circuit board layout and protection device placement:

Circuit board layout is critical for the suppression of ESD, EFT and Surge transients. The following guidelines are recommended:

1. Place the protection device as close to the input terminal or connector as possible.
2. The path length between the protection device and the protected line should be minimized.
3. Keep parallel signal paths to a minimum.
4. Avoid running protection conductors in parallel with unprotected conductor.
5. Minimize all printed-circuit board conductive loops including power and ground loops.
6. Minimize the length of the transient return path to ground.
7. Avoid using shared transient return paths to a common ground point.
8. Ground planes should be used whenever possible. For multilayer printed-circuit boards, use ground vias.

8. Package outline

Plastic surface mounted package; 2 leads

SOD523

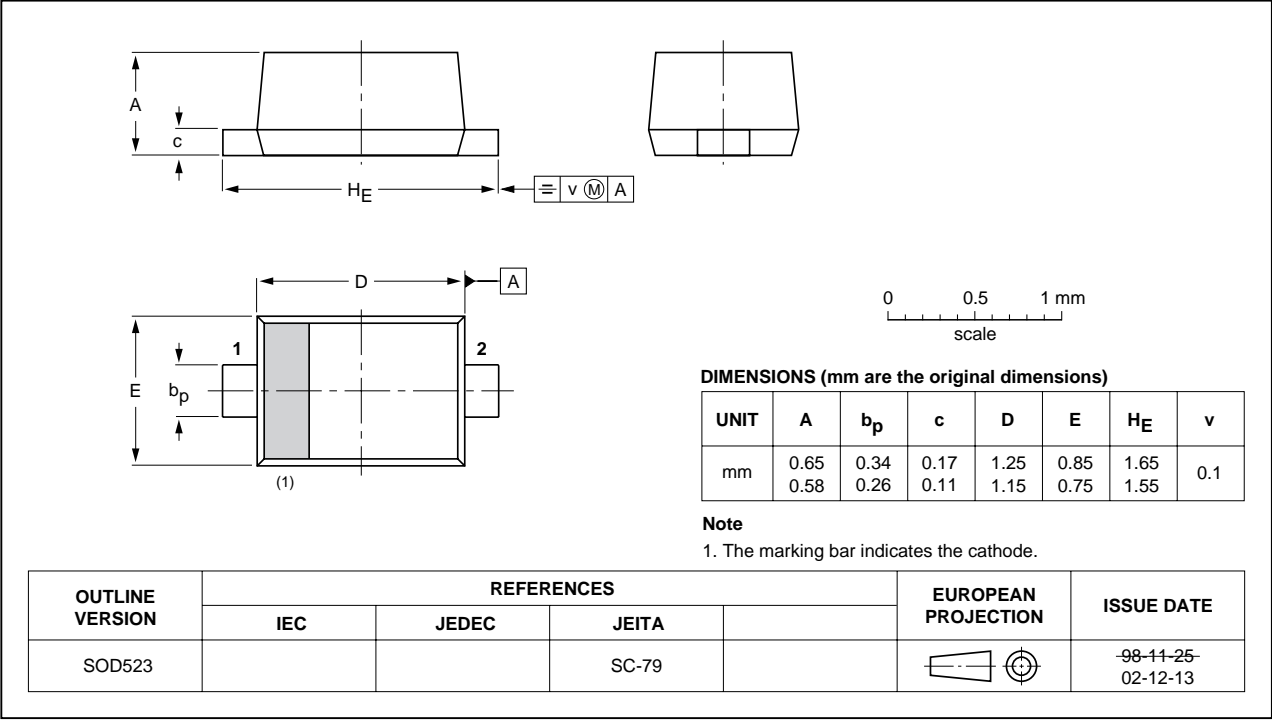


Fig 10. Package outline.

## 9. Packing information

**Table 9: Possible packing methods**

The indicated -xxx are the last three digits of the 12 NC ordering code. [\[1\]](#)

| Type number | Package | Description                    | Packing quantity |       |
|-------------|---------|--------------------------------|------------------|-------|
|             |         |                                | 3000             | 10000 |
| PESD3V3S1UB | SOD523  | 4 mm pitch, 8 mm tape and reel | -115             | -135  |
| PESD5V0S1UB | SOD523  | 4 mm pitch, 8 mm tape and reel | -115             | -135  |
| PESD12VS1UB | SOD523  | 4 mm pitch, 8 mm tape and reel | -115             | -135  |
| PESD15VS1UB | SOD523  | 4 mm pitch, 8 mm tape and reel | -115             | -135  |
| PESD24VS1UB | SOD523  | 4 mm pitch, 8 mm tape and reel | -115             | -135  |

[1] For further information see [Section 14](#).



10. Revision history

Table 10: Revision history

| Document ID        | Release date | Data sheet status | Change notice | Order number   | Supersedes |
|--------------------|--------------|-------------------|---------------|----------------|------------|
| PESDxS1UB_series_1 | 20040614     | Product data      | -             | 9397 750 13313 | -          |

## 11. Data sheet status

| Level | Data sheet status <sup>[1]</sup> | Product status <sup>[2]</sup> <sup>[3]</sup> | Definition   |
|-------|----------------------------------|--|--|
| I     | Objective data                   | Development                                  | This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.  |
| II    | Preliminary data                 | Qualification                                | This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.             |
| III   | Product data                     | Production                                   | This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN). |

[1] Please consult the most recently issued data sheet before initiating or completing a design.

[2] The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL <http://www.semiconductors.philips.com>.

[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

## 12. Definitions

**Short-form specification** — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

**Limiting values definition** — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

**Application information** — Applications that are described herein for any of these products are for illustrative purposes only. Philips Semiconductors make no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

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